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PATENT APPLICATION

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of

Hiroji AGA et al.

Group Art Unit: 2823

Application No.: 09/857,803

Examiner: M. Estrada

Filed: June 11, 2001

Docket No.: 109725

For: METHOD FOR PRODUCING SOI WAFER AND SOI WAFER

REQUEST FOR RECONSIDERATION

Director of the U.S. Patent and Trademark Office
Washington, D.C. 20231

Sir:

In reply to the Office Action mailed March 14, 2002, reconsideration of the rejections under 35 U.S.C. §103(a) is respectfully requested in light of the following remarks.

REMARKS

Claims 1-9 are pending herein.

I. Rejections under §103

A. Yamamoto (JP-10275905) and Takada (JP-10335616)

Claims 1 and 2 are rejected under 35 U.S.C. §103(a) as allegedly unpatentable over Yamamoto and Takada et al. Applicants respectfully traverse this rejection.

The Office Action asserts that Yamamoto teaches a method for producing an SOI wafer by the hydrogen ion delamination method comprising bonding a substrate member to a silicon wafer member, in which a hydrogen implanted layer is formed by gas ion implantation, and delaminating the silicon wafer member, bound to the substrate member, along the implanted hydrogen layer. The delaminated surface of the wafer is then annealed in a hydrogen atmosphere to planarize the delaminated surface. However, the Office Action

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